

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING BODY
BIASING CIRCUIT FOR GENERATING FORWARD WELL BIAS
VOLTAGE OF SUITABLE LEVEL BY USING SIMPLE CIRCUITRY

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ABSTRACT OF THE DISCLOSURE

10 A semiconductor integrated circuit device has a MISFET and a body biasing circuit. The MISFET has a source electrode and a drain electrode of a first conductivity type and a gate electrode, and the MISFET is formed in a well of a second conductivity type. The body 15 biasing circuit generates a voltage in the well by passing a prescribed current in a forward direction into a diode which is formed from the well and the source electrode of the MISFET.